## In the Specification

At page 1 before the "Technical Field" section, please insert the following:

## RELATED PATENT DATA

This patent resulted from a divisional application of U.S. Patent Application Serial No. 10/051,678, filed January 16, 2002, entitled "Method of Forming Integrated Circuitry, Semiconductor Processing Methods, and Processing Method of Forming MRAM Circuitry", naming Li, Li, Max F. Hineman and Mark E. Tuttle as inventor(s), the disclosure of which is incorporated by reference.